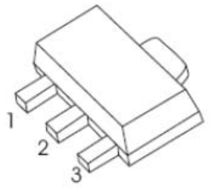
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89-3L Plastic-Encapsulate Transistors

KTC4375 TRANSISTOR (NPN)

SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

Low voltage

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	0.5	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

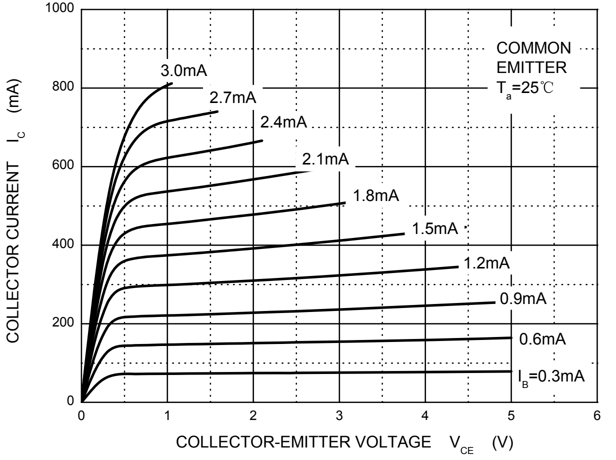
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=1mA,I_E=0	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=30V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=2V,I_C=0.5A	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=1.5A,I_B=30mA			2	V
Base-emitter voltage	V_{BE}	V_{CE}=2V,I_C=0.5A			1	V
Transition frequency	f_T	V_{CE}=2V,I_C=500mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz			40	pF

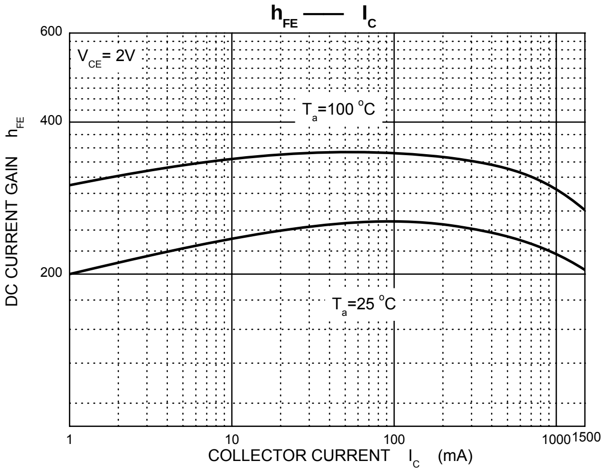
CLASSIFICATION OF $h_{FE(1)}$

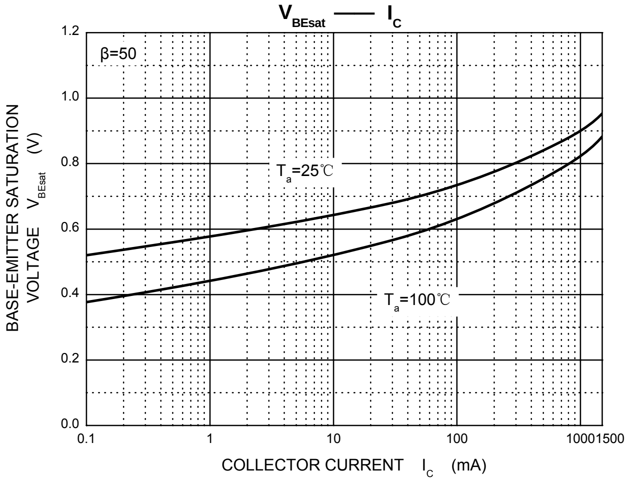
Rank	O	Y
Range	100-200	160-320
Marking	GO	GY

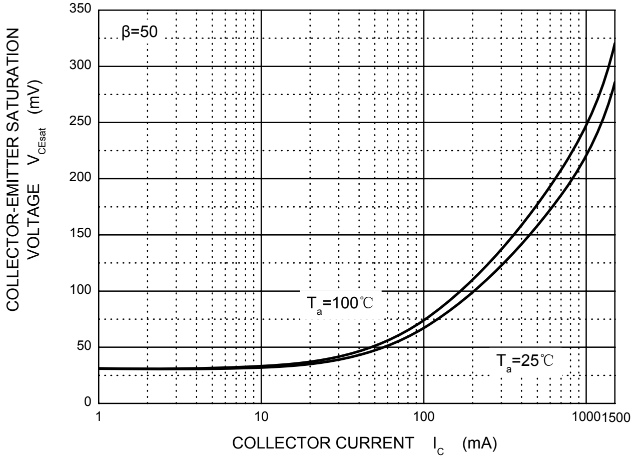
B,Jun,2012

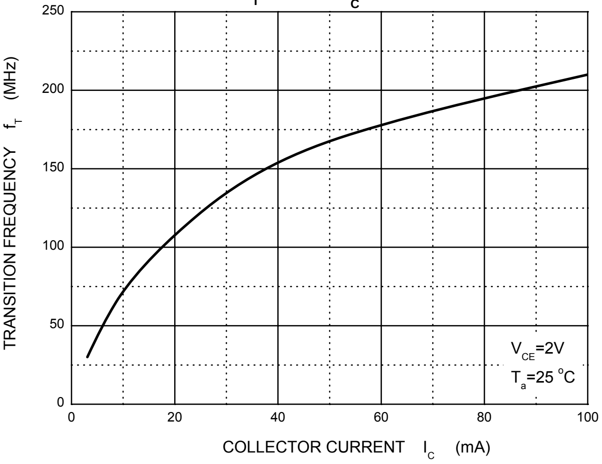
Typical Characteristics KTC4375

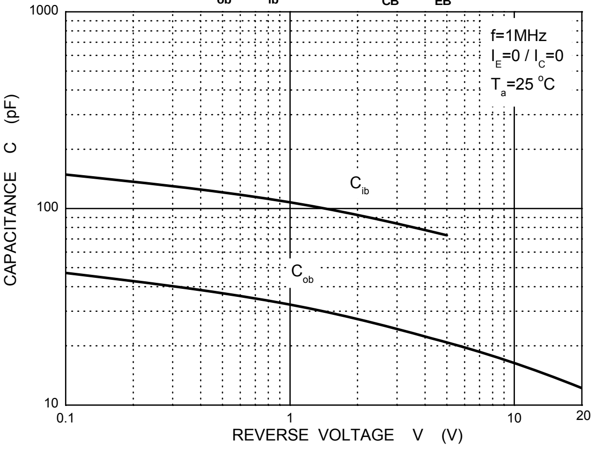

Static Characteristic

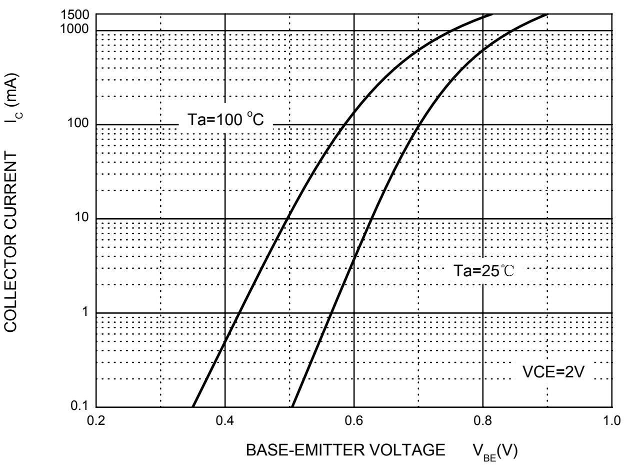

h_{FE} — I_C

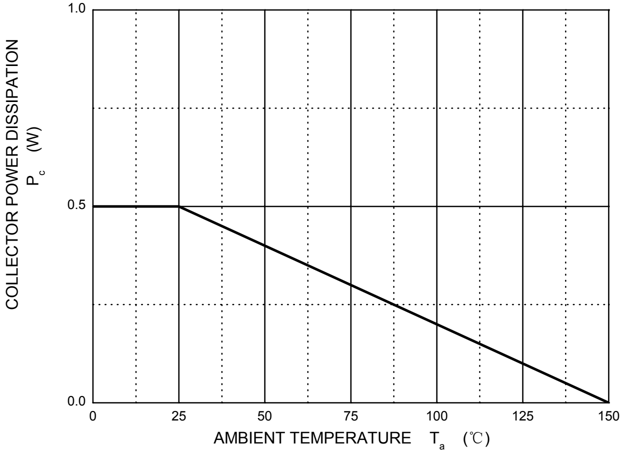

V_{BEsat} — I_C


V_{CEsat} — I_C


f_T — I_C


C_{ob} / C_{ib} — V_{CB} / V_{EB}


V_{BE} — I_C


P_c — T_a